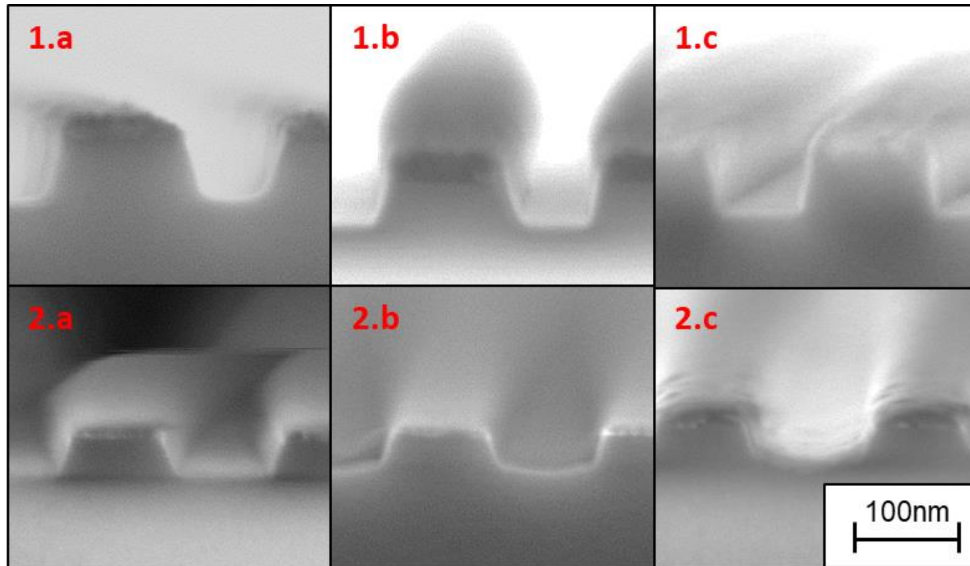

Figure 1. SiO_2 etching of 100 nm features with 60 cycles CHF_3-based ALE using different masks. Raw 1: 70 nm ZEP; Raw 2:10 nm lift-off Chromium (Cr). SiO_2 features have been etched using CHF_3-based ALE at different Ar^+ ions powers during the removal step (Figure 1(d) and (e)). Column 1: DC_{bias} = 25 V; Column 2: DC_{bias} = 22 V; Column 3: DC_{bias} = 17 V.